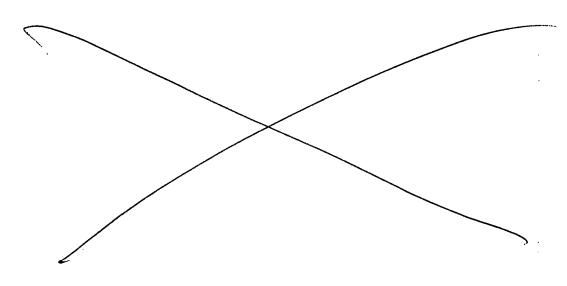
Sheet <u>1</u> of <u>1</u>

Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 14564-006002	Application No. /ひ/ファダ, 0(9	
Information Disclosure Statement by Applicant (Use several sheets if necessary)		Applicant (
		Filing Date	Group Art Unit	
(37 CFR §1.98(b))				

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
DW	AA	5,661,742	Aug. 26, 1997	Huang et al.			

	Other Documents (include Author, Title, Date, and Place of Publication)				
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Initial	ID	Document			
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	Examiner Signature **Market Signature** **Proposition of the content of the con	Date Considered 9/7//0 /			
I	EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.				